

ABSTRACT OF THE DISCLOSURE

The present invention relates to a test pattern for measuring a contact resistance and method of manufacturing the same. In order to confirm that a

5 contact resistance suitable for a semiconductor device before an actual process for manufacturing the device is performed, the present invention designs a test pattern for measuring the contact resistance depending on a design rule of a line contact actually applied to an actual device. At this time, a first line

10 contact region and a second line contact region are formed between a word line so that a line contact region can form a pair; a plurality of sources are formed in the first line contact region and a plurality of sources are formed in the second line contact region wherein neighboring sources are connected by

15 diffusion layers so that the first line contact region and the second line contact region can be electrically connected; and a plurality of line contact patterns are formed so that the plurality of the sources can be electrically connected by

20 every two in each of the first and second line contact regions wherein the line contact pattern formed in the first line contact region and the line contact pattern formed in the second line contact region are alternately positioned. Therefore, the present invention can allow current for measuring the resistance sequentially along the first line contact region and the second line contact region to measure the line contact resistance in which the contact resistance in every source portion is considered.